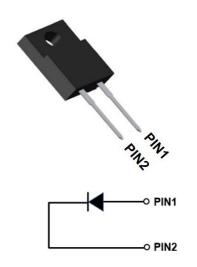


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (96°C)}	10A
Qc	58nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

 Package: ITO-220AC
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112010FGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _C =25°C			14.6
Continuous forward current @ T _C =96°C	I _F	Α	10
Continuous forward current @ T _C =135°C			6.5
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	83
Power Dissipation@ T _C =25°C	D.	\	38
Power Dissipation@ T _C =110°C	P _{TOT}	W	16
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	34
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =10A, T _j =25°C	1.38	1.55
			I _F =10A, T _j =175°C	2	-
Reverse leakage current	I _R	μΑ	V _R =1200V, T _j =25°C	1	20
			V _R =1200V, T _j =175°C	8	-
Total capacitive charge	Qc	nC	V_R =800V, T_j =25°C , Q_C = $\int_0^{VR} C(V) dV$	58	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	813	-
			V _R =400V, f=1MHZ	54	-
			V _R =800V, f=1MHZ	40	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	15	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	3.90

■Typical Characteristics

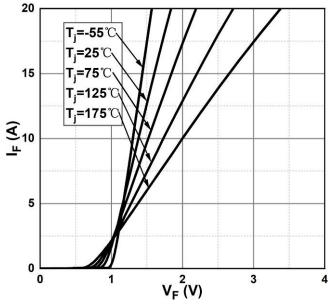


Figure 1. Forward Characteristics

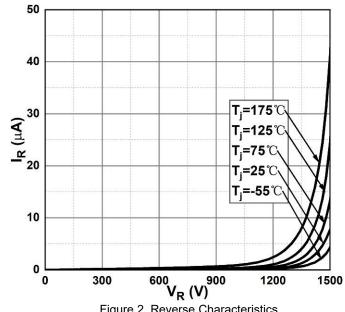
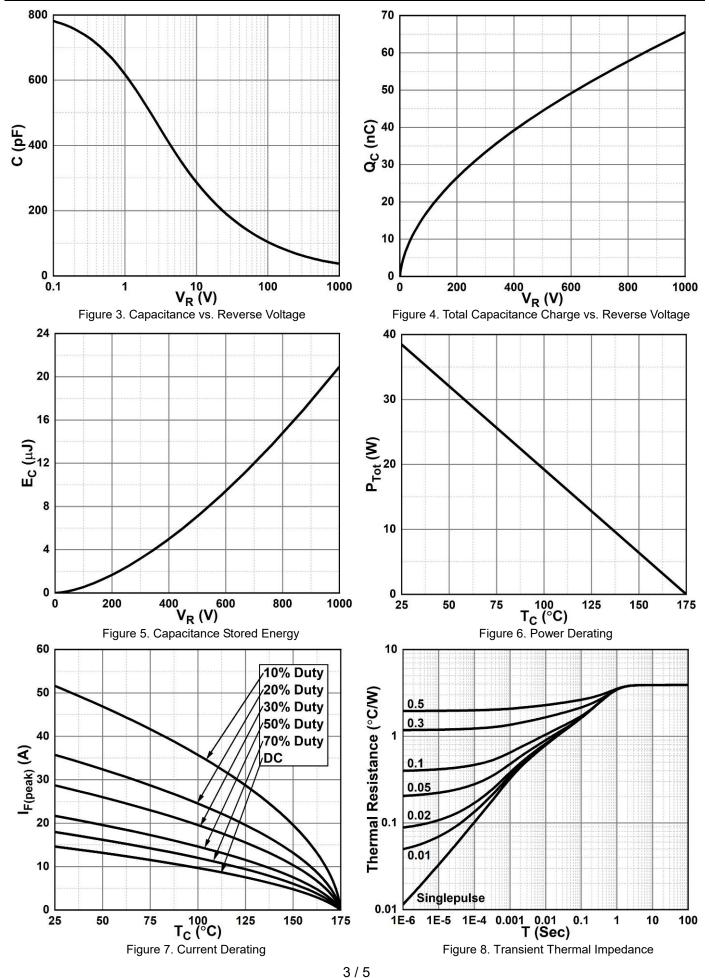


Figure 2. Reverse Characteristics

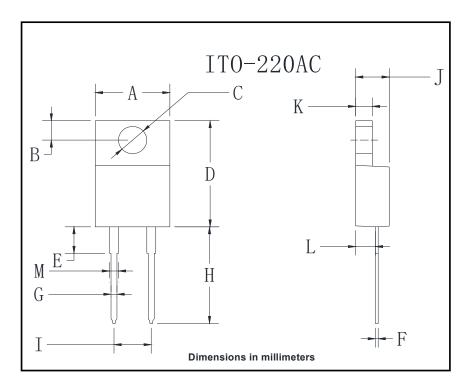








■Outline Dimensions



ITO-220AC				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
E	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
K	2.5	2.74		
L	2.58	2.82		
М	1.03	1.43		



YJD112010FGH



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